

IT(RMS)		75A
VDRM/VRRM		1200V
VTM		1.5V

FEATURES

IT(RMS): 75A

VGT: 1.3V

VDRM VRRM:1200V

High Junction Temperature

Good Commutation Performance

APPLICATIONS

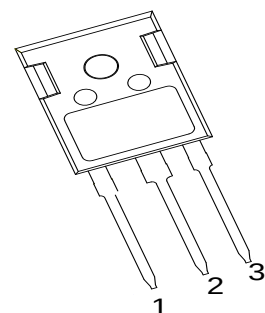
Heater Control

Motor Speed Controller

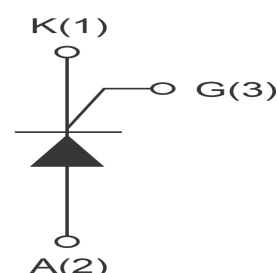
Washing machine

Vacuums

Solid state relay



TO-247J



Absolute Maximum Ratings (Tj=25°C unless otherwise specified)

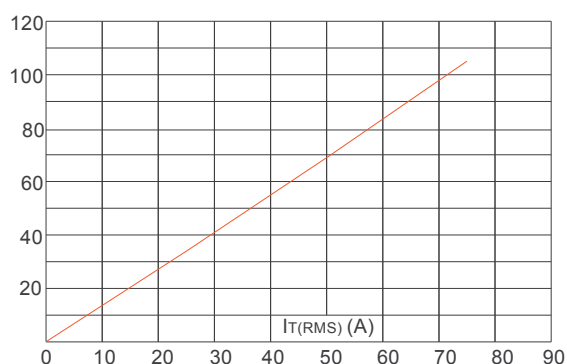
Symbol	Parameter	Conditions	Ratings	Unit
VDRM VRRM	Repetitive Peak Off-State Voltage	TYN7512	1200	V
		TYN7516	1600	V
IT(RMS)	R.M.S On-State Current		75	A
ITSM	Surge On-State Current	F=50Hz, tp=10ms/8.3ms	800	A
I ² t	I ² t for fusing	tp=10ms	3200	A ² s
PG(AV)	Average Gate Power Dissipation	Tj=125°C	1	W
PGM	Peak Gate Current	Tj=125°C	5	W
IGM	Peak Gate Current	tp=10us	4	A
Tj	Operating Junction Temperature		~40~125	°C
TSTG	Storage Temperature		~40~150	°C

Electrical Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Value	Unit
IDRM	Repetitive Peak Off-State Current	T _c =25°C	≤50	uA
		T _c =125°C	≤10	mA
IRRM	Repetitive Peak Reverse Current	T _c =25°C	≤50	uA
		T _c =125°C	≤10	mA
VTM	Forward "on" voltage	I _T =60A tp=380us	≤1.5	V
VGD	Gate nontrigger voltage	V _D =V _{DRM} , T _j =125°C, R _L =3.3KΩ	≥0.2	V
IL	Latching current	I _G =1.2I _{GT}	≤150	mA
IH	Holding current	V _D =12V, I _{GT} =0.1A	≤120	mA
VGT	Gate trigger voltage	V _D =12V	≤1.3	V
IGT	Gate trigger current	V _D =12V, I _T =0.1A	≤70	mA
dv/dt	Critical-rate of rise of commutation voltage	V _D =2/3V _{DRM} , T _j =125°C, gate open circuit	≥700	V/us
di/dt	Critical-rate of rise of commutation current	I _G =2X I _G , tr100us, T _j =125°C	≥150	A/us
Rth(j-c)	Thermal resistance	Junction to case	0.53	°C/W

FIG1

Maximum power dissipation versus RMS on-state current


FIG2

RMS on-state current versus case temperature

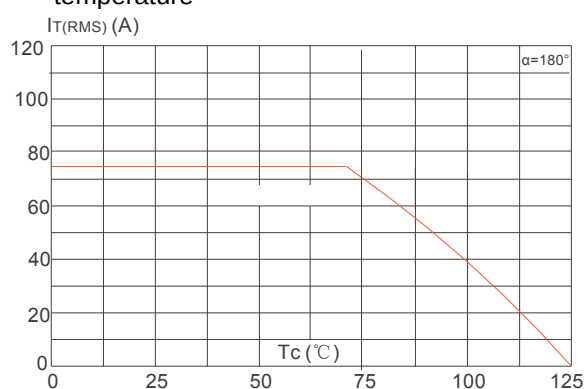


FIG3

Surge peak on-state current versus number of cycles

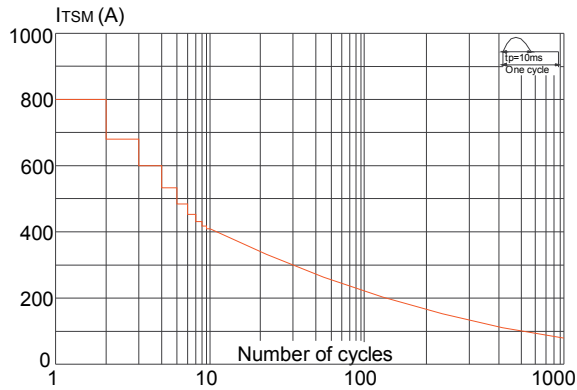


FIG4

On-state characteristics (maximum values)

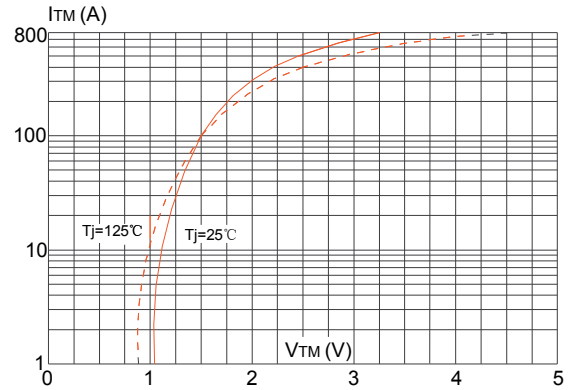


FIG5

Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($dI/dt < 100A/\mu s$)

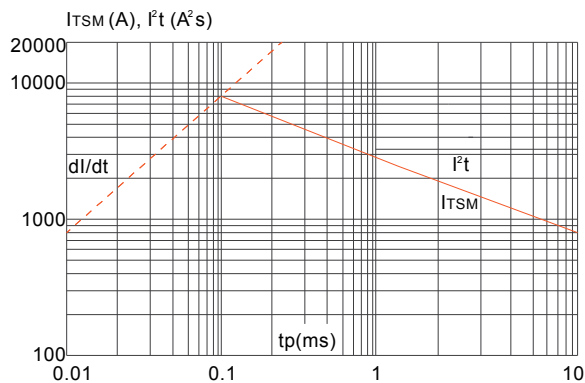


FIG6

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

